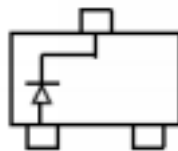
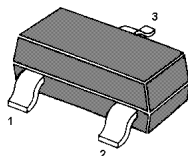
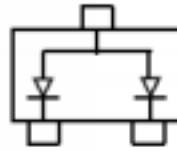


Silicon Epitaxial Planar Switching Diode

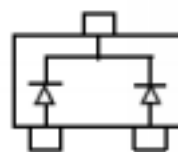
SOT-23



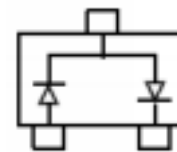
BAS21



BAS21A



BAS21C



BAS21S

Marking: BAS21 JS

Marking: BAS21A JS2

Marking: BAS21C JS3

Marking: BAS21S JS4

Maximum Ratings @T_A=25°C

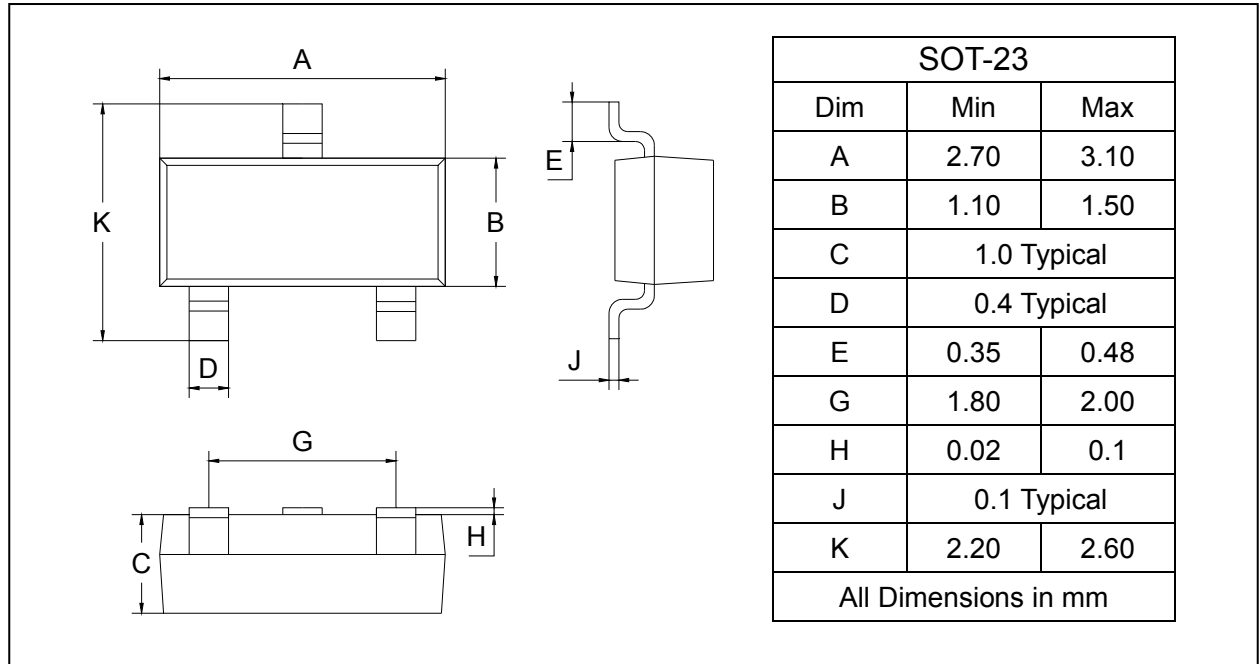
Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V _{RRM}	250	V
Working Peak reverse voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Forward Continuous Current	I _{FM}	400	mA
Average Rectified Output Current	I _O	200	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0μs	I _{FSM}	2.5	A
@ t = 1.0s		0.5	
Repetitive Peak Forward Surge Current	I _{FRM}	625	mA
Power Dissipation	P _D	225	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	556	°C/W
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-65-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

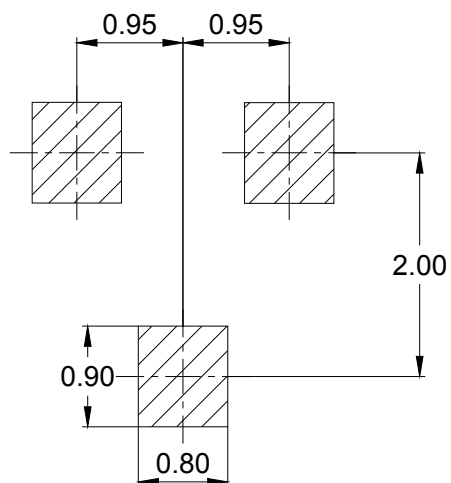
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 100μA	250		V
Reverse voltage leakage current	I _R	V _R =200V		1	μA
Forward voltage	V _F	I _F =100mA I _F =200mA		1000 1250	mV
Diode capacitance	C _D	V _R =0V, f=1MHz		5	pF
Reveres recovery time	t _{rr}	I _F =I _R =30mA, I _{rr} =0.1×I _R , R _L =100Ω		50	nS

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



Unit : mm

